

# **Product Specification**

# XBLW SN74AHC1G04

Single Inverter









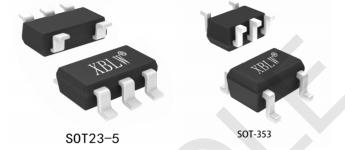


# **Description**

The SN74AHC1G04 is a high-speed Si-gate CMOS devices. Provide a inverting buffer.

### **Feature**

- ➤ Specified from -40°C to +125°C
- ➤ Packaging information: SOT-23-5/SOT-353
- > Low power consumption
- Operating range 2 V to 5.5 V



# **Applications**

- Cameras
- E-Meters
- > Infotainment
- > Ethernet Switches

# **Ordering Information**

Product Model	Package Type	Package Type Marking		Packing Qty	
XBLW SN74AHC1G04T235	SOT-23-5	CBXX	Таре	3000Pcs/Reel	
XBLW SN74AHC1G04T353	SOT-353	CBXX	Tape	3000Pcs/Reel	



# **Block Diagram**

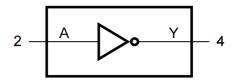


Figure 1. Logic symbol

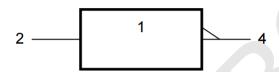
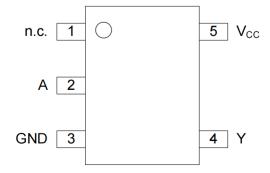


Figure 2.ICE Logic symbol



Figure 3.ICE Logic diagram

# **Pin Configurations**





# **Pin Description**

Pin No.	Pin Name	Description
1	n.c.	not connected
2	A	data input
3	GND	ground (0V)
4	Y	data output
5	Vcc	supply voltage

# **Function Table**

Input	Output
A	Y
L	Н
Н	L

Note: H=HIGH voltage level; L=LOW voltage level.

# **Electrical Parameter**

### **Absolute Maximum Ratings**

(Voltages are referenced to GND(ground=oV), unless otherwise specified.)

Parameter	Symbol	Conditions	Min.	Max.	Unit
supply voltage	$V_{CC}$	-	-0.5	+7.0	V
input voltage	$V_{\rm I}$	-	-0.5	+7.0	V
input clamping current	$I_{1K}$	$V_1 < -0.5V$	-20	-	mA
output clamping current	$I_{OK}$	Vo< -0.5V or Vo>Vcc+0.5V	-	±20	mA
output current	$I_0$	$-0.5V < V_0 < V_{CC} + 0.5V$	-	±25	mA
supply current	$I_{CC}$	-	-	75	mA
ground current	$I_{GND}$	-	-75	-	mA
storage temperature	$T_{\mathrm{stg}}$	-	-65	+150	°C
total power dissipation	P <sub>tot</sub>		-	250	mW
Soldering T <sub>L</sub> temperature		10s	20	50	°C



### **Recommended Operating Conditions**

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
supply voltage	$V_{CC}$	-	2.0	5.0	5.5	V
input voltage	$V_{\rm I}$	-	0	-	5.5	V
output voltage	$V_0$	-	0	-	Vcc	V
ambient temperature	$T_{amb}$	-	-40	-	+125	°C
input transition rise	A + / A T/	Vcc=3.0V to 3.6V	-	-	100	ns/V
and fall rate	∆t/∆V	Vcc=4.5V to 5.5V	-	-	20	ns/V

# **ESD Ratings**

Parameter		Defintion	Vaue	Unit	
V(ESD)	Electrostatic	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins (1)	±2000	V	
V (ESD)	discharge	Charged device model (CDM), per JEDEC specification JESD22-C101, all pins (2)	±1000	V	

JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control (1)

# **Electrical Characteristics**

### **DC** Characteristics 1

 $(T_{amb}=25\,^{\circ}\text{C}$ , voltages are referenced to GND (ground=oV), unless otherwise specified.)

Parameter	Symbol		Conditions	Min.	Тур.	Max.	Unit
HIGH 1			$V_{cc}=2.0V$	1.5		-	V
HIGH-level input voltage	V <sub>IH</sub>	Vcc=3.0V		2.1		-	V
			Vcc=5.5V	3.85		-	V
			Vcc=2.0V	-		0.5	V
LOW-level input voltage	$V_{IL}$		Vcc=3.0V	-		0.9	V
voltage			Vcc=5.5V	-		1.65	V
			Io=-50uA; Vcc=2.0V	1.9	2.0		V
HIGH I		$V_{I} = V_{IH} \text{ or } V_{IL}$	Io=-50uA; Vcc=3.0V	2.9	3.0		V
HIGH-level output voltage	V <sub>OH</sub>		Io=-50uA; Vcc=4.5V	4.4	4.5		V
Voltage			Io=-4mA; Vcc=3.0V	2.58	-		V
			Io=-8mA; Vcc=4.5V	3.94	-		V
	V <sub>OL</sub>	$V_{OL}$ $V_{I} = V_{IH} \text{ or } V_{IL}$	Io=50uA; Vcc=2.0V		0	0.1	V
LOWIS			Io=50uA; Vcc=3.0V		0	0.1	V
LOW-level output voltage			Io=50uA; Vcc=4.5V		0	0.1	V
Voltage			Io=4mA; Vcc=3.0V		-	0.36	V
			Io=8mA; Vcc=4.5V		-	0.36	V
input leakage current	II		5.5V or GND; c=0V to 5.5V	-	-	1.0	uA
supply current	I <sub>CC</sub>		Vi=Vcc or GND; Io=0A; Vcc= 5.5V		-	1.0	uA
input capacitance	Cı		-	-	1.5	10	pF

process. (2) J JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



### DC Characteristics 2

 $(T_{amb}=-40 \,^{\circ}\text{C} \text{ to } +85 \,^{\circ}\text{C}, \text{ voltages are referenced to GND (ground=0V), unless otherwise specified.)}$ 

Parameter	Symbol		Conditions	Min.	Тур.	Max.	Unit
THE CITY I		Vcc=2.0V		1.5		-	V
HIGH-level input voltage	VIH		Vcc=3.0V	2.1		-	V
voltage			Vcc=5.5V	3.85		-	V
			Vcc=2.0V	-		0.5	V
LOW-level input voltage	$V_{IL}$		Vcc=3.0V	-		0.9	V
vortage			Vcc=5.5V	-		1.65	V
			Io=-50UA; Vcc=2.0V	1.9			V
HIGH 11	ut V <sub>OH</sub>	$V_{I} = V_{IH}$ or $V_{IL}$	Io=-50UA; Vcc=3.0V	2.9			V
HIGH-level output voltage			Io=-50uA; Vcc=4.5V	4.4			V
vortage			Io=-4mA; Vcc=3.0V	2.48			V
			Io=-8mA; Vcc=4.5V	3.8			V
		$V_{OL}$ $V_{I} = V_{IH} \text{ or } V_{IL}$	Io=50uA; Vcc=2.0V			0.1	V
LOW-level output			Io=50uA; Vcc=3.0V			0.1	V
voltage	$V_{OL}$		Io=50uA; Vcc=4.5V			0.1	V
vortage			Io=4mA; Vcc=3.0V			0.44	V
			Io=8mA; Vcc=4.5V			0.44	V
input leakage current	l <sub>l</sub>		V <sub>1</sub> =5.5V or GND; Vcc=0V to 5.5V		-	1.0	uA
supply current	Icc		e or GND; Io=0A; Vcc= 5.5V	-	-	10	uA
input capacitance	Cı			-	-	10	pF

### DC Characteristics 3

( $T_{amb}$ =-40 °C to +125 °C, voltages are referenced to GND (ground=0V), unless otherwise specified.)

Parameter	Symbol		Conditions	Min.	Тур.	Max.	Unit
THOU I			Vcc=2.0V	1.5		-	V
HIGH-level input voltage	$V_{IH}$	Vcc=3.0V		2.1		-	V
			Vcc=5.5V	3.85		-	V
			Vcc=2.0V	-		0.5	V
LOW-level input voltage	VIL		Vcc=3.0V	-		0.9	V
voltage			Vcc=5.5V	-		1.65	V
			Io=-50uA; Vcc=2.0V	1.9			V
IIICII I I	V <sub>ОН</sub>	$V_I = V_{IH}$ or $V_{IL}$	Io=-50uA; Vcc=3.0V	2.9			V
HIGH-level output voltage			Io=-50uA; Vcc=4.5V	4.4			V
			Io=-4mA; Vcc=3.0V	2.4			V
			Io=-8mA; Vcc=4.5V	3.7			V
	VoL	$V_{I} = V_{IH} \text{ or } V_{IL}$	Io=50uA; Vcc=2.0V			0.1	V
I OW level enteret			Io=50uA; Vcc=3.0V			0.1	V
LOW-level output voltage			Io=50uA; Vcc=4.5V			0.1	V
voluge			Io=4mA; Vcc=3.0V			0.55	V
			Io=8mA; Vcc=4.5V			0.55	V
input leakage current	II		5.5V or GND; c=0V to 5.5V	-	-	2.0	uA
supply current	I <sub>CC</sub>		e or GND; Io=0A; Vcc= 5.5V	_	-	40	uA
input capacitance	Cı			-	-	10	pF



#### **AC Characteristics 1**

(T<sub>amb</sub>=25°C, voltages are referenced to GND (ground=0V), unless otherwise specified.)

Parameter	Symbol		Conditions	Min.	Тур.	Max.	Unit
			Vcc=3.0V to 3.6V				
		see Figure 5	G=15pF	ı	4.3	7.1	ns
A to Y propagation	t <sub>pd</sub>		CL=50pF	1	6.1	10.6	ns
delay			Vcc=4.5V to 5.5V				
			G=15pF	ı	3.1	5.5	ns
			CL=50pF	ı	4.5	7.5	ns
Power dissipation capacitance	$C_{PD}$	C <sub>L</sub> =50pF;	$f_i$ =1MHz; $V_I$ =GND $\sim V_{CC}$	-	15	-	pF

#### Note:

[1]tpd is the same as tphL and tpLH.

[2]Typical values are measured at Vcc=3.3V or 5V.

[3] CPD is used to determine the dynamic power dissipation (PD in uW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$  where:

fi=input frequency in MHz;

fo=output frequency in MHz;

CL=output loadcapacitance in pF;

Vcc=supply voltage in V;

 $\sum (C_L \times V_{CC}^2 \times f_0)$ =sum of outputs.

#### **AC Characteristics 2**

(T<sub>amb</sub>=-40 °C to +85 °C, voltages are referenced to GND (ground=0 V), unless otherwise specified.)

	Parameter	Symbol		Conditions	Min.	Тур.	Max.	Unit
	A to Y propagation			Vcc=3.0V to 3.6V				
		gation t <sub>pd</sub>		G=15pF	1.0	-	8.5	ns
			see Figure 5	CL=50PF	1.0	-	12	ns
	delay			Vcc=4.5V to 5.5V				
				CL=15PF	1.0	-	6.5	ns
				CL=50PF	1.0	-	8.5	ns

### Note:

- [1] tpd is the same as tPHL and tPLH.
- [2] Typical values are measured at Vcc=3.3V or 5V.

#### **AC Characteristics 3**

 $(T_{amb}=-40 \,^{\circ}\text{C} \text{ to } +125 \,^{\circ}\text{C}, \text{ voltages are referenced to GND (ground=0V), unless otherwise specified.)}$ 

Parameter	Symbol		Conditions	Min.	Тур.	Max.	Unit
			Vcc=3.0V to 3.6V				
			C <sub>L</sub> =15 <sub>P</sub> F	1.0	-	11	ns
A to Y propagation	<b>.</b>	see Figure 5	CL=50PF	1.0	-	14.5	ns
delay	t <sub>pd</sub>	see Figure 3	Vcc=4.5V to 5.5V				
			C <sub>L</sub> =15 <sub>P</sub> F	1.0	-	7.0	ns
			CL=50PF	1.0	-	9.5	ns

### Note:

- [1] tpd is the same as tPHL and tPLH.
- [2] Typical values are measured at Vcc=3.3V or 5V.



# **Testing Circuit**

### **AC Testing Circuit**

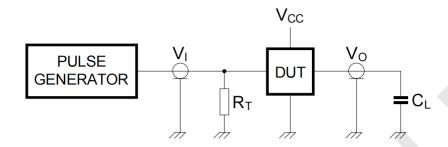


Figure 4. Load circuitry for switching times

Definitions for test circuit:

CL=Load capacitance including jig and probe capacitance.

RT=Termination resistance should be equal to output impedance Zo of the pulse generator.

# **AC Testing Waveforms**

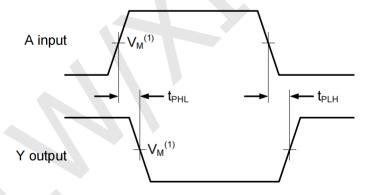


Figure 5. The input (A) to output (Y) propagation delay times

#### **Measurement Points**

Tyno	Inj	Output	
Туре	$\mathbf{V}_{\mathbf{I}}$	$\mathbf{V}_{\mathbf{M}}$	$\mathbf{V}_{\mathbf{M}}$
SN74AHC1G04	GND to Vcc	0.5xVcc	0.5xVcc

### **Test Data**

Inj	Load	
Vı	$t_{ m r}$ , $t_{ m f}$	CL
GND to Vcc	< 3.0ns	15pF
GND to Vcc	< 3.0ns	50pF



# **Package Information**

• SOT23-5

	Dimensions In	Millimeters	SIZE	Dimensions	In Inches
SYMBOL	MIN(mm)	MAX (mm)	SYMBOL	MIN(in)	MAX(in)
A	1.050	1.250	A	0.041	0.049
A1	0.000	0.100	A1	0.000	0.004
A2	1.050	1. 150	A2	0.041	0.045
b	0.300	0.500	b	0.012	0.020
С	0.100	0.200	С	0.004	0.008
D	2.820	3. 020	D	0.111	0.119
Е	1. 500	1.700	E	0. 059	0.067
E1	2.650	2.950	E1	0. 104	0.116
е		5 (BSC)	е	0. 037 (BSC)	
e1	1.800	2.000	e1	0.071	0.079
L	0.300	0.600	L	0.012	0.024
θ	0°	8°	θ	0°	8°
EI		e e1		c	
A					



# • SOT-353

	T				. 1	
Size	Dimensions In Millimeters		Size	Dimensions In Inches		
Symbol	Min(mm)	Max(mm)	Symbol _	Min(in)	Max(in)	
A	0.900	1. 100	A	0.035	0.043	
A1	0.000	0. 100	A1	0.000	0.004	
A2	0.900	1.000	A2	0.035	0.039	
b	0. 150	0.350	b	0.006	0.014	
С	0.080	0. 150	С	0.003	0.006	
D	2.000	2. 200	D	0.079	0.087	
E	1. 150	1.350	E	0.045	0.053	
E1	2. 150	2. 450	E1	0.085	0.096	
e		50 (TYP)	е	0. 026 (TYP)		
e1	1. 200	1. 400	e1	0.047	0.055	
L		25 (REF)	L		021 (REF)	
L1	0. 260	0. 460	L1	0.010	0.018	
θ	0°	8°	θ	0°	8°	
el e e l e l e l e l e l e l e l e l e						



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